

High-Frequency Amplifier Transistor

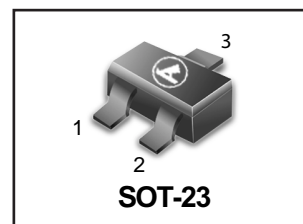
DESCRIPTION

The L2SC3356LT1 is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

It has dynamic range and good current characteristic.

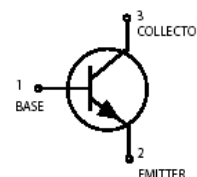
ORDERING INFORMATION

Device	Marking	Shipping
L2SC3356LT1G	R24	3000/Tape & Reel
L2SC3356LT3G	R24	10000/Tape & Reel

L2SC3356LT1G


FEATURES

- We declare that the material of product compliance with RoHS requirements.
- Low Noise and High Gain
 $NF = 1.1 \text{ dB TYP.}, G_a = 11 \text{ dB TYP. @ } V_{CE} = 10 \text{ V}, I_c = 7 \text{ mA}, f = 1.0 \text{ GHz}$
- High Power Gain
 $MAG = 13 \text{ dB TYP. @ } V_{CE} = 10 \text{ V}, I_c = 20 \text{ mA}, f = 1.0 \text{ GHz}$



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Collector to Base Voltage	V _{CB0}	20	V
Collector to Emitter Voltage	V _{CEO}	12	V
Emitter to Base Voltage	V _{EBO}	3.0	V
Collector Current	I _c	100	mA
Total Power Dissipation	P _T	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I _{CB0}			1.0	μA	V _{CB} = 10 V, I _E = 0
Emitter Cutoff Current	I _{EBO}			1.0	μA	V _{EB} = 1.0 V, I _C = 0
DC Current Gain	h _{FE}	82	170	270		V _{CE} = 10 V, I _C = 20 mA
Gain Bandwidth Product	f _T		7		GHz	V _{CE} = 10 V, I _C = 20 mA
Feed-Back Capacitance	C _{re} **		0.55	1.0	pF	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz
Insertion Power Gain	S _{21e} ²		11.5		dB	V _{CE} = 10 V, I _C = 20 mA, f = 1.0 GHz
Noise Figure	NF		1.1	2.0	dB	V _{CE} = 10 V, I _C = 7 mA, f = 1.0 GHz

* Pulse Measurement PW ≤ 350 μs, Duty Cycle ≤ 2 %

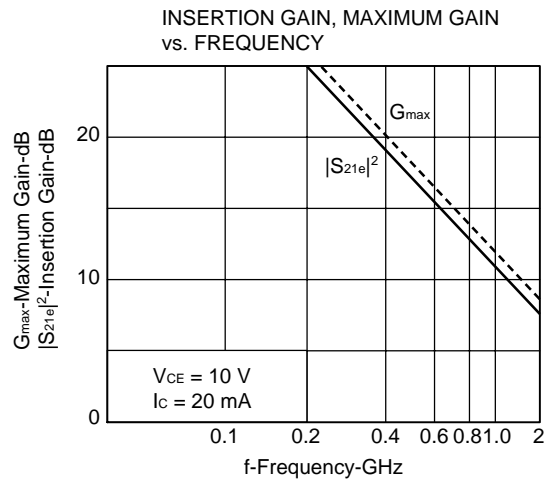
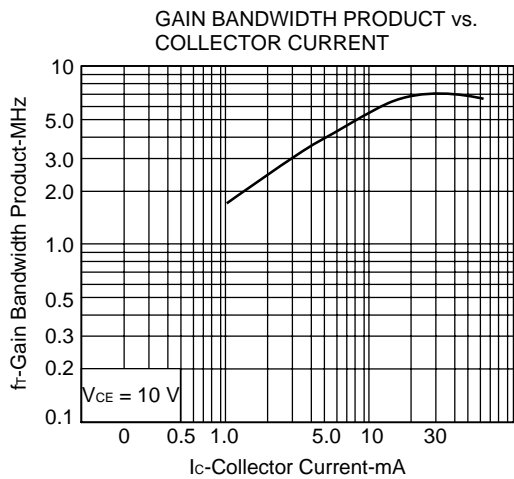
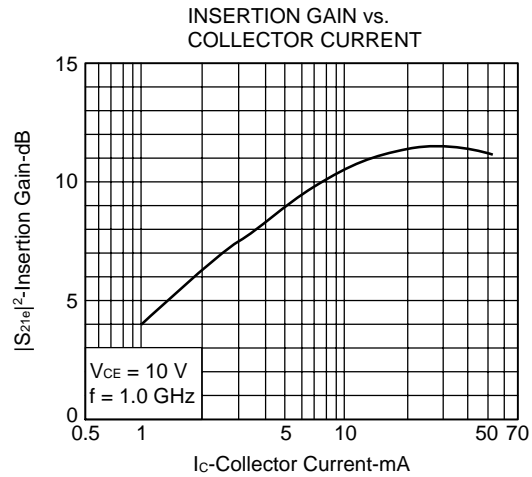
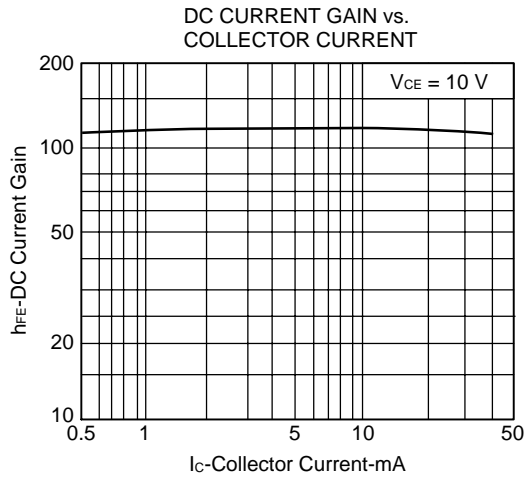
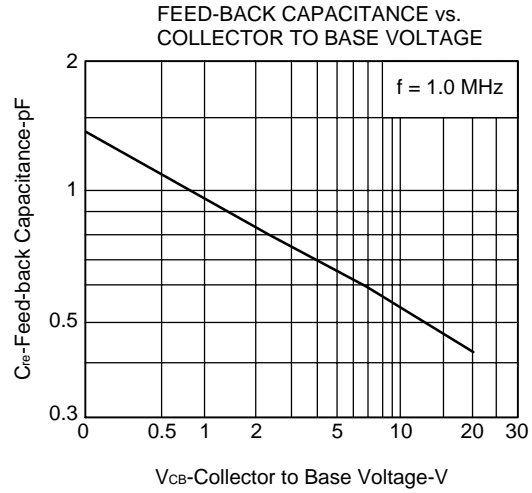
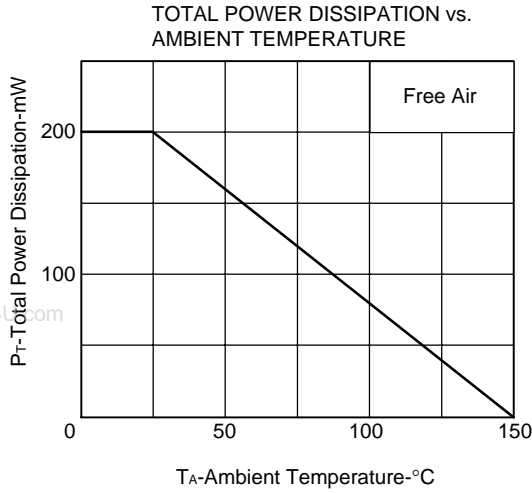
* The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

Driver Marking

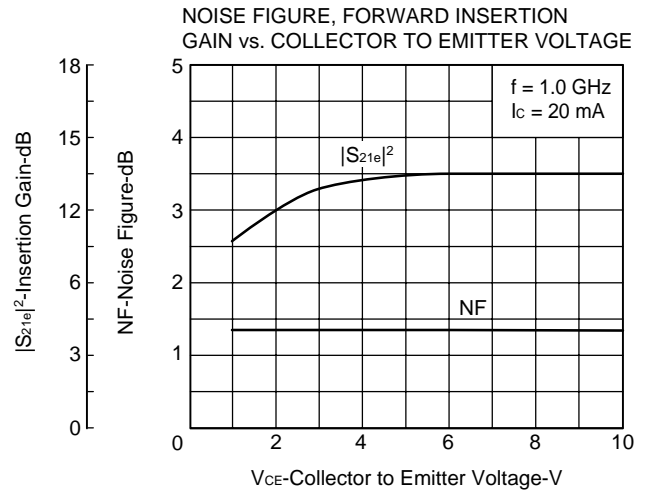
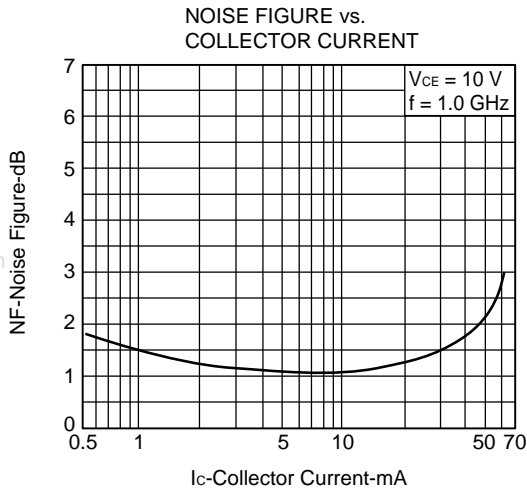
L2SC3356LT1G=R24

TYPICAL CHARACTERISTICS (T_A = 25 °C)

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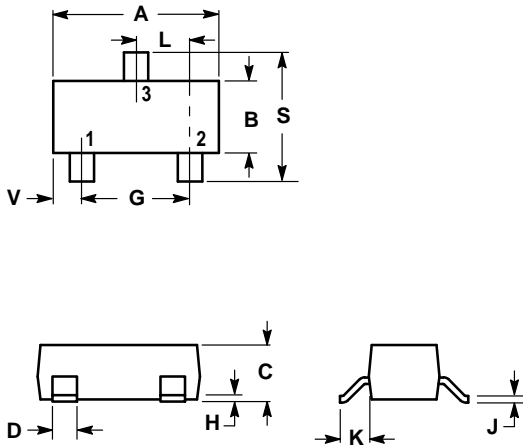
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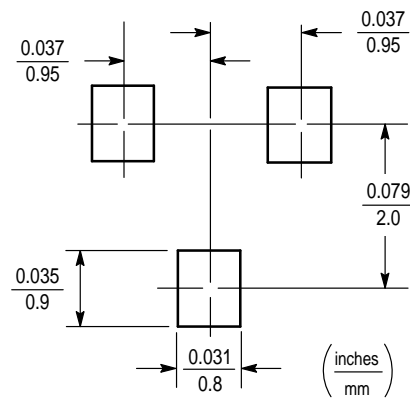


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

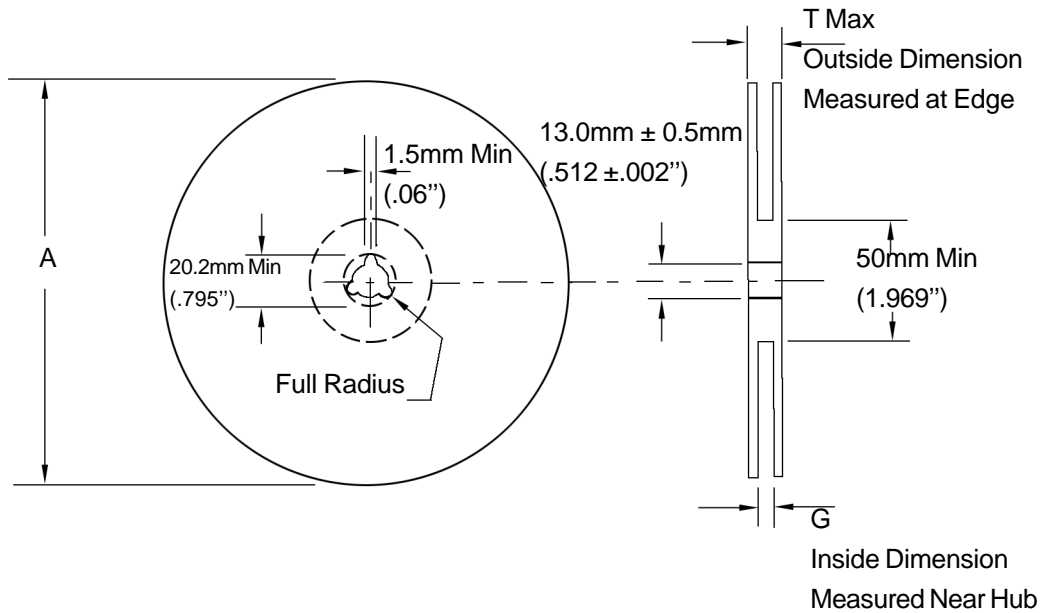
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
 2. EMITTER
 3. COLLECTOR



EMBOSSED TAPE AND REEL DATA FOR DISCRETES

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Size	A Max	G	T Max
8 mm	330mm (12.992")	8.4mm+1.5mm, -0.0 (.33"+.059", -0.00)	14.4mm (.56")

Reel Dimensions

Metric Dimensions Govern — English are in parentheses for reference only

Storage Conditions

Temperature: 5 to 40 Deg.C (20 to 30 Deg. C is preferred)

Humidity: 30 to 80 RH (40 to 60 is preferred)

Recommended Period: One year after manufacturing

(This recommended period is for the soldering condition only. The characteristics and reliabilities of the products are not restricted to this limitation)

Shipment Specification

